

Session Title: [TA3] RF Power Amplifier

Session Date: December 4 (Thu.), 2025

Session Time: 13:20-15:00

Session Room: Room A (Halla A)

[TA3-1] [Invited] 13:20-13:40

#### An Improved Noise Figure Measurement Technique for Differential Amplifiers

Bharatha Kumar Thangarasu, Shuai Li, Hongshi Yu, Wansi Ge, Xiaozheng Guo, Yuqing Liu, Sini Wu, Nagarajan Mahalingam, Fanyi Meng and Kaixue Ma (Tianjin University, China); Luz Hh (Suda, China); Kiat Seng Yeo (Singapore University of Technology and Design, Singapore & Tianjin University, China)

[TA3-2] 13:40-14:00

### A Reconfigurable Dual-Band Asymmetrical Doherty Power Amplifier Using PIN Diodes

Gongxu He and Cuiping Yu (Beijing University of Posts and Telecommunications, China); Yuanan Liu (Beijing University of Posts and Telecom, China)

[TA3-3] 14:00-14:20

#### A Ka-Band Harmonic-Tuned GaN Doherty Power Amplifier

Moise Safari Mugisho and Christian Friesicke (Fraunhofer IAF, Germany); Dirk Schwantuschke (Fraunhofer Institute for Applied Solid State Physics, Germany); Peter Brückner and Rüdiger Quay (Fraunhofer IAF, Germany)

[TA3-4] 14:20-14:40

## **Novel Inductively-Gated FET Diodes for Microwave Rectifiers**

Taisei Shimada and Shinichi Tanaka (Shibaura Institute of Technology, Japan)

[TA3-5] 14:40-15:00

# Asymmetric Doherty Power Amplifier Design Based on Load-Pull Driven Current Ratio Optimization for Accurate Load Modulation

Jisu Park and Minjae Ahn (Konkuk University, Korea (South)); Dongsu Kim and Yunsik Park (Korea Electronics Technology Institute, Korea (South)); Hyunchul Ku (Konkuk University, Korea (South))